

IN THE CLAIMS:

Please enter the following amended claims, noting that a marked-up version is shown in the Appendix:

8<sup>1</sup> 2. (Twice Amended) A semiconductor structure for electrostatic discharge (ESD) protection of a metal-oxide semiconductor (MOS) integrated circuit comprising:

a substrate of a first conductivity type forming a base for said semiconductor structure;

a first region of a second conductivity type within said substrate for forming a drain of a first MOS transistor;

a second region of the second conductivity type within said substrate for forming a source of the first MOS transistor;

a third region of the second conductivity type within said substrate for forming a source of a second MOS transistor, wherein

a fourth region of the first conductivity type is disposed between the second region of said first MOS transistor and the third region of said second MOS transistor for surrounding said first MOS transistor with an additional pick-up diffusion to restrain the turn-on of said first MOS transistor, and

wherein the channel length of said first MOS transistor is longer than the channel length of said second MOS transistor to increase the drain-base voltage of said first MOS transistor.

3. (Amended) The semiconductor structure of claim 1, further comprising:

a pre-buffer circuit coupled to a gate of the first MOS transistor; and

an output pad coupled to said first region of the first MOS transistor.

4. (Twice Amended) A semiconductor structure for electrostatic discharge (ESD) protection of a metal-oxide semiconductor (MOS) integrated circuit comprising:

a substrate of a first conductivity type forming a base for said semiconductor structure;

a first region of a second conductivity type with said substrate for forming a drain of a first MOS transistor;

a second region of the second conductivity type within said substrate for forming a source of the first MOS transistor;

a third region of the second conductivity type within said substrate for forming a source of a second MOS transistor, wherein a fourth region of the first conductivity type is disposed between the second region of said first MOS transistor and the third region of said second MOS transistor for surrounding said first MOS transistor with an additional pick-up diffusion to restrain the turn-on of said first MOS transistor;

a first channel region disposed between said first and second regions of said first MOS transistor; and

a second channel region disposed adjacent to said third region of said second MOS transistor,

wherein said first channel length of said first channel region is longer than the channel length of said second channel region to increase the drain-base breakdown voltage of said first MOS transistor.

B<sup>2</sup>

7. (Twice Amended) A semiconductor structure for electrostatic discharge (ESD) protection of a metal-oxide semiconductor (MOS) integrated circuit comprising:

a substrate of a first conductivity type forming a base for said semiconductor structure;

a pair of first regions of a second conductivity type within said substrate for defining a first channel region of the second conductivity type for a first MOS transistor;

a pair of second regions of the second conductivity type within said substrate for defining a second channel region of the second conductivity type for a second MOS transistor, wherein the channel length of said first channel region is greater than the channel length of said second channel region to reduce a turn-on speed of said first MOS transistor; and

a third region of the first conductivity type between the source side of said first regions and the source side of said second regions for surrounding said first MOS transistor with an additional pick-up diffusion to further restrain the turn-on speed of said first MOS transistor.

B<sup>3</sup>

9. (Twice Amended) A semiconductor structure for electrostatic discharge (ESD) protection of a metal-oxide semiconductor (MOS) integrated circuit comprising:

a p-type substrate of forming a base for said semiconductor structure;

a first N<sup>+</sup> region within said substrate for forming a drain of a first MOS transistor;

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a second N<sup>+</sup> region within said substrate for forming a source of the first MOS transistor;

a third N<sup>+</sup> region within said substrate for forming a source of a second MOS transistor,

wherein a P<sup>+</sup> region is disposed between the second N<sup>+</sup> region of said first MOS transistor and the third N<sup>+</sup> region of said second MOS transistor for surrounding said first MOS transistor with an additional pick-up diffusion to restrain the turn-on speed of said first MOS transistor, and

wherein the channel length of said first MOS transistor is longer than the channel length of said second MOS transistor to increase a drain-base breakdown voltage of said first MOS transistor.

10. (Amended) The semiconductor structure of claim 8, further comprising:

a pre-buffer circuit coupled to a gate of the first MOS transistor; and

an output pad coupled to said first region of the first MOS transistor.

11. (Twice Amended) A semiconductor structure for electrostatic discharge (ESD) protection of a metal-oxide semiconductor (MOS) integrated circuit comprising:

a p-type substrate of forming a base for said semiconductor structure;

a first N<sup>+</sup> region within said substrate for forming a drain of a first MOS transistor;

a second N<sup>+</sup> region within said substrate for forming a source of the first MOS transistor;

B2  
cont.

a third N<sup>+</sup> region within said substrate for forming a source of a second MOS transistor, wherein a P<sup>+</sup> region is disposed between the second N<sup>+</sup> region of said first MOS transistor and the third N<sup>+</sup> region of said second MOS transistor for surrounding said first MOS transistor with an additional pick-up diffusion to restrain the turn-on speed of said first MOS transistor;

a first n-channel region having a first channel length and disposed between said first and second regions of said first MOS transistor; and

a second n-channel region having a second channel length disposed adjacent to said third region of said second MOS transistor,

wherein said first channel length is longer than said second channel length to further increase the drain-base breakdown voltage of said first MOS transistor.

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B3

14. (Twice Amended) A semiconductor structure for electrostatic discharge (ESD) protection of a metal-oxide semiconductor (MOS) integrated circuit comprising:

a p-type substrate forming a base for said semiconductor structure;

a pair of first N<sup>+</sup> regions within said substrate for defining a first n-channel region for a first MOS transistor;

a pair of second N<sup>+</sup> regions within said substrate for defining a second n-channel region for a second MOS transistor, wherein the channel length of said first channel is greater than the channel length of said second channel; and

a third P<sup>+</sup> region between the source region of said first N<sup>+</sup> regions and the source region of said second N<sup>+</sup> regions for surrounding said first MOS transistor with an additional pick-up diffusion to further restrain the turn-on of said first MOS transistor.

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34

19. (Amended) A semiconductor structure for electrostatic discharge (ESD) protection comprising:

at least one ESD protection device; and

at least one guarded device which is turned-on by a turn-on restrained means,

wherein the ESD protection device can be turned-on before the turn-on restrained means is turned-on.

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